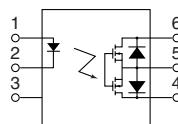
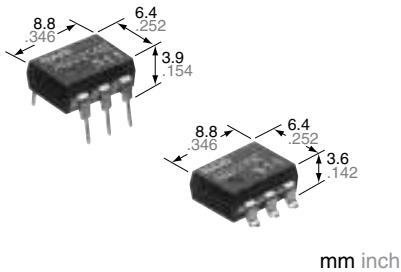


Panasonic
ideas for life

General use and economy type.
DIP (1 Form A) 6-pin type.
Reinforced insulation
5,000V type.

GU-E PhotoMOS
(AQV210E,
AQV210EH)

FEATURES



- 1. Controls low-level analog signals**
PhotoMOS relays feature extremely low closed-circuit offset voltage to enable control of low-level analog signals without distortion.
- 2. Control with low-level input signals**
- 3. Controls various types of loads such as relays, motors, lamps and solenoids.**
- 4. Optical coupling for extremely high isolation**
Unlike mechanical relays, the PhotoMOS relay combines LED and optoelectronic device to transfer signals using light for extremely high isolation.
- 5. Eliminates the need for a counter electromotive force protection diode in the drive circuits on the input side**

- 6. Stable on resistance**
- 7. Low-level off state leakage current**
- 8. Eliminates the need for a power supply to drive the power MOSFET**
A power supply used to drive the power MOSFET is unnecessary because of the built-in optoelectronic device. This results in easy circuit design and small PC board area.
- 9. Low thermal electromotive force (Approx. 1 μ V)**

TYPICAL APPLICATIONS

- High-speed inspection machines
- Telephone equipment
- Data communication equipment
- Computer

TYPES

Type	I/O isolation	Output rating*		Part No.				Packing quantity	
				Through hole terminal		Surface-mount terminal			
		Load voltage	Load current	Tube packing style		Tape and reel packing style		Tube	Tape and reel
AC/DC	Standard 1,500 V AC	350 V	130 mA	AQV210E	AQV210EA	AQV210EAX	AQV210EAZ	1 tube contains 50 pcs.	1,000 pcs.
		400 V	120 mA	AQV214E	AQV214EA	AQV214EAX	AQV214EAZ		
	Reinforced 5,000 V	350 V	130 mA	AQV210EH	AQV210EHA	AQV210EHAX	AQV210EHAZ	1 batch contains 500 pcs.	
		400 V	120 mA	AQV214EH	AQV214EHA	AQV214EHAX	AQV214EHAZ		

*Indicate the peak AC and DC values.

Note: For space reasons, the SMD terminal shape indicator "A" and the package type indicator "X" and "Z" are omitted from the seal.

RATING

1. Absolute maximum ratings (Ambient temperature: 25°C 77°F)

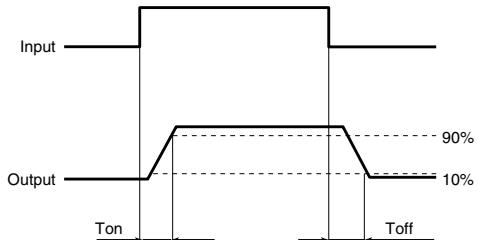
Item		Symbol	Type of connection	AQV210E(A)	AQV214E(A)	AQV210EH(A)	AQV214EH(A)	Remarks
Input	LED forward current	I _F	\	50 mA				
	LED reverse voltage	V _R		5 V				
	Peak forward current	I _{FP}		1 A				f = 100 Hz, Duty factor = 0.1%
	Power dissipation	P _{in}		75 mW				
Output	Load voltage (peak AC)	V _L	A	350 V	400 V	350 V	400 V	
	Continuous load current	I _L		0.13 A	0.12 A	0.13 A	0.12 A	A connection: Peak AC, DC; B, C connection: DC
				0.15 A	0.13 A	0.15 A	0.13 A	
	Peak load current	I _{peak}	C	0.17 A	0.15 A	0.17 A	0.15 A	A connection: 100 ms (1 shot), V _L =DC
	Power dissipation	P _{out}		500 mW				
Total power dissipation		P _T		550 mW				
I/O isolation voltage		V _{iso}		1,500 V AC		5,000 V AC		
Temperature limits	Operating	T _{opr}		-40°C to +85°C		-40°F to +185°F		Non-condensing at low temp.
	Storage	T _{stg}		-40°C to +100°C		-40°F to +212°F		

GU-E PhotoMOS (AQV210E, AQV210EH)

2. Electrical characteristics (Ambient temperature: 25°C 77°F)

Item			Symbol	Type of connection	AQV210E(A)	AQV214E(A)	AQV210EH(A)	AQV214EH(A)	Condition		
Input	LED operate current		Typical	I_{Fon}	1.1 mA			1.6 mA			
	Maximum				3 mA			$I_L = \text{Max.}$			
	LED turn off current		Minimum	I_{Foff}	0.3 mA			0.4 mA			
	Typical				1.0 mA			$I_L = \text{Max.}$			
Output	LED dropout voltage		Typical	V_F	1.25 V (1.14 V at $I_F = 5 \text{ mA}$)						
	Maximum				1.5 V						
	On resistance		Typical	R_{on}	A	23 Ω	30 Ω	23 Ω	30 Ω		
	Maximum					35 Ω	50 Ω	35 Ω	50 Ω		
	Typical		Typical	R_{on}	B	11.5 Ω	22.5 Ω	11.5 Ω	22.5 Ω		
	Maximum					17.5 Ω	25 Ω	17.5 Ω	25 Ω		
	Typical		Typical	R_{on}	C	6.0 Ω	11.3 Ω	6.0 Ω	11.3 Ω		
	Maximum					8.8 Ω	12.5 Ω	8.8 Ω	12.5 Ω		
Output capacitance		Typical	C_{out}	A	45 pF						
Off state leakage current		Maximum	—	—	1 μA						
Transfer characteristics	Switching speed	Turn on time*	T_{on}	—	0.5 ms		0.7 ms		$I_F = 0 \text{ mA} \rightarrow 5 \text{ mA}^{**}$		
		Maximum			2.0 ms		$I_L = \text{Max.}$				
	Turn off time*	Typical	T_{off}	—	0.05 ms		$I_F = 0 \text{ mA} \rightarrow 5 \text{ mA}$				
		Maximum			1.0 ms		$I_L = \text{Max.}$				
	I/O capacitance		C_{iso}	—	0.8 pF		$f = 1 \text{ MHz}$				
	Maximum				1.5 pF		$V_B = 0 \text{ V}$				
Initial I/O isolation resistance		Minimum	R_{iso}	—	1,000 MΩ						
					500 V DC						

*Turn on/Turn off time



** Recommendable LED forward current

Standard type: 5 mA

Reinforced type: 5 to 10 mA

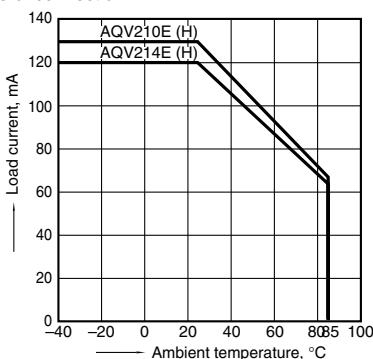


REFERENCE DATA

1. Load current vs. ambient temperature characteristics

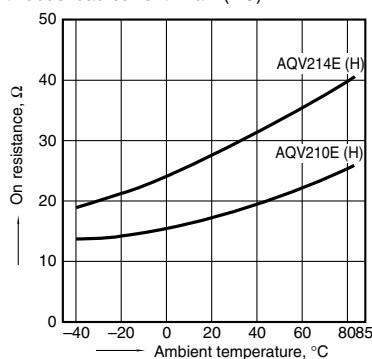
Allowable ambient temperature: -40°C to +85°C
-40°F to +185°F

Type of connection:A



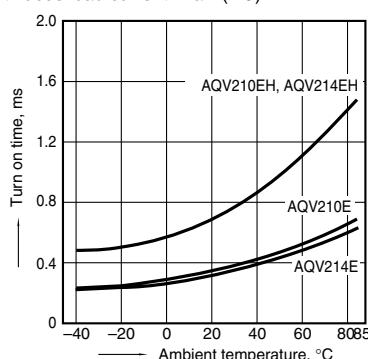
2. On resistance vs. ambient temperature characteristics

Measured portion: between terminals 4 and 6;
LED current: 5 mA; Load voltage: Max. (DC);
Continuous load current: Max. (DC)



3. Turn on time vs. ambient temperature characteristics

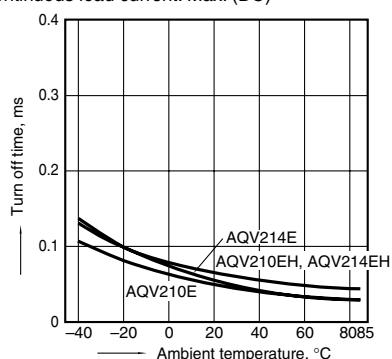
LED current: 5 mA;
Load voltage: Max. (DC);
Continuous load current: Max. (DC)



GU-E PhotoMOS (AQV210E, AQV210EH)

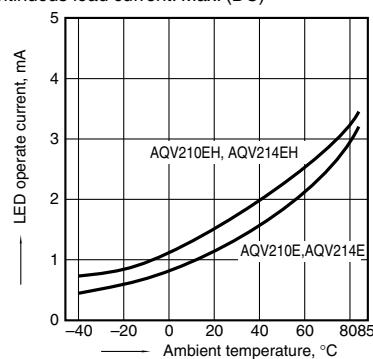
4. Turn off time vs. ambient temperature characteristics

LED current: 5 mA; Load voltage: Max. (DC); Continuous load current: Max. (DC)



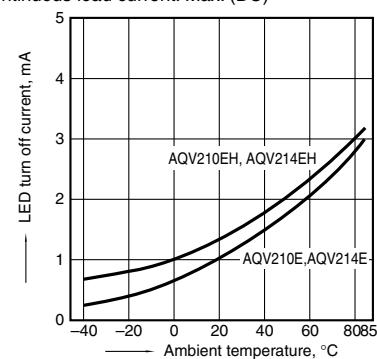
5. LED operate current vs. ambient temperature characteristics

Load voltage: Max. (DC); Continuous load current: Max. (DC)



6. LED turn off current vs. ambient temperature characteristics

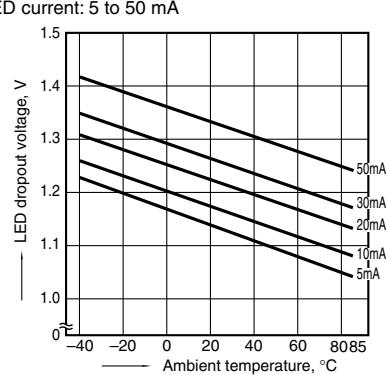
Load voltage: Max. (DC); Continuous load current: Max. (DC)



7. LED dropout voltage vs. ambient temperature characteristics

Sample: All types

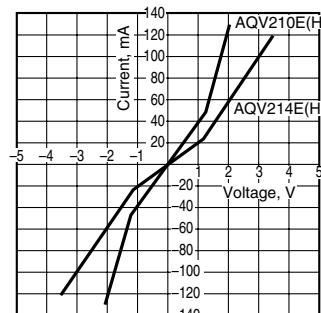
LED current: 5 to 50 mA



8. Current vs. voltage characteristics of output at MOS portion

Measured portion: between terminals 4 and 6;

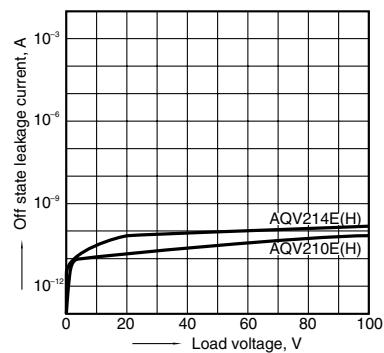
Ambient temperature: 25°C 77°F



9. Off state leakage current vs. load voltage characteristics

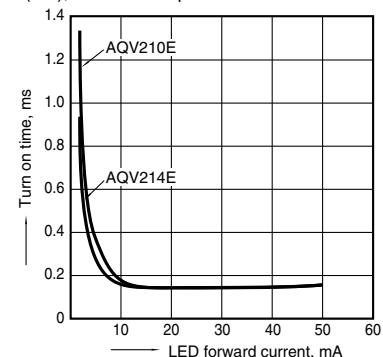
Measured portion: between terminals 4 and 6;

Ambient temperature: 25°C 77°F



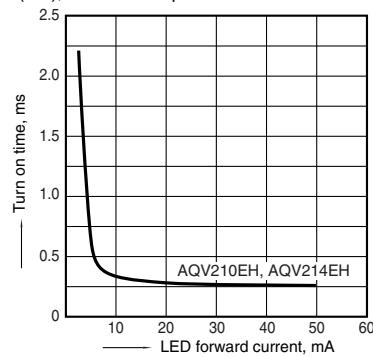
10-(1). Turn on time vs. LED forward current characteristics

Measured portion: between terminals 4 and 6; Load voltage: Max. (DC); Continuous load current: Max. (DC); Ambient temperature: 25°C 77°F



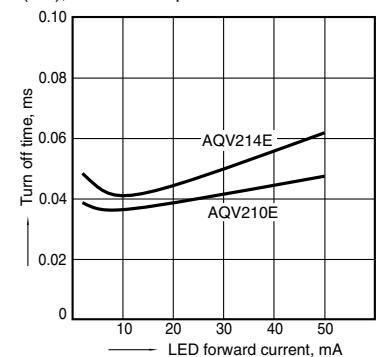
10-(2). Turn on time vs. LED forward current characteristics

Measured portion: between terminals 4 and 6; Load voltage: Max. (DC); Continuous load current: Max. (DC); Ambient temperature: 25°C 77°F



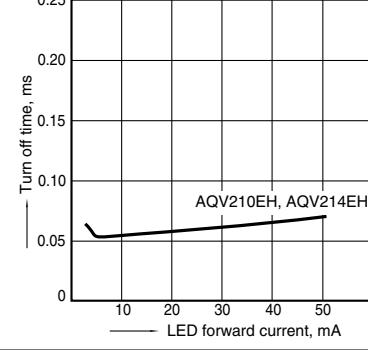
11-(1). Turn off time vs. LED forward current characteristics

Measured portion: between terminals 4 and 6; Load voltage: Max. (DC); Continuous load current: Max. (DC); Ambient temperature: 25°C 77°F



11-(2). Turn off time vs. LED forward current characteristics

Measured portion: between terminals 4 and 6; Load voltage: Max. (DC); Continuous load current: Max. (DC); Ambient temperature: 25°C 77°F



12. Output capacitance vs. applied voltage characteristics

Measured portion: between terminals 4 and 6; Frequency: 1 MHz; Ambient temperature: 25°C 77°F

